

SII NanoTechnology Inc.
FIB Application

Low Acceleration Mode Processing

Damage reduction in FIB processing

The relationship between FIB acceleration voltage and damaged sample layer thickness

5kV



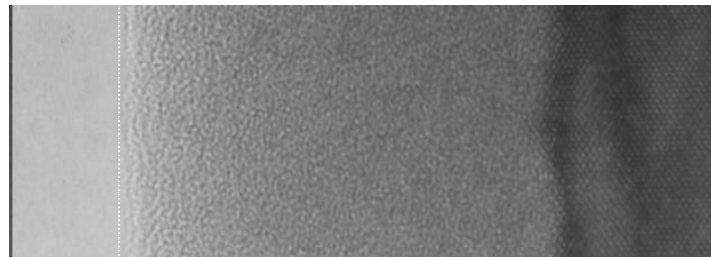
Damaged layer = 6.6nm

15kV



Damaged layer = 14.4nm

30kV



Damaged layer = 23.3nm

Si surface